

## RB520S-30

### Silicon Epitaxial Planar Schottky Barrier Diode

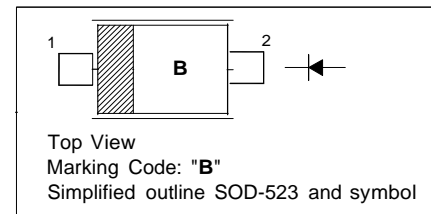
for low current rectification and high speed switching applications

#### Features

- Extremely small surface mounting type
- High reliability

#### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



#### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	30	V
Mean Rectifying Current	$I_{F(AV)}$	200	mA
Peak Forward Surge Current (60 Hz for 1 Cyc.)	$I_{FSM}$	1	A
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 40 to + 125	$^\circ\text{C}$

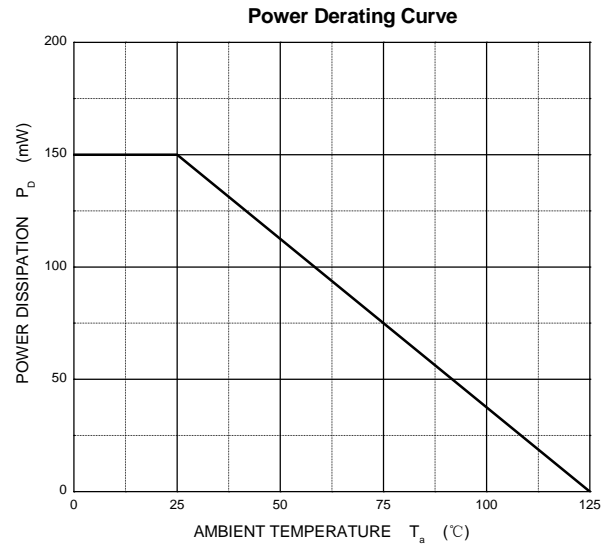
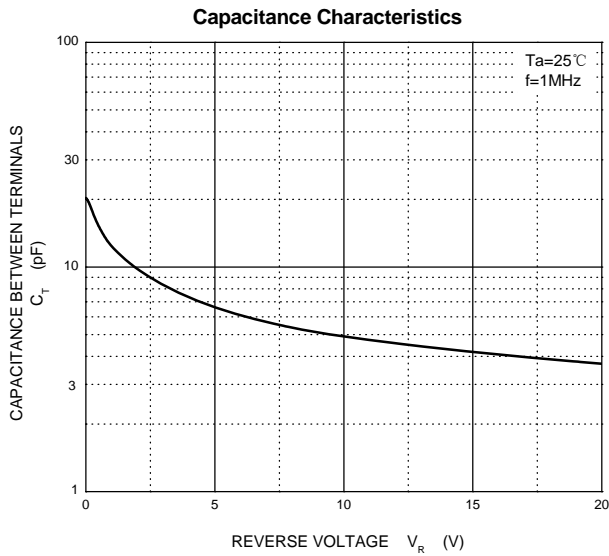
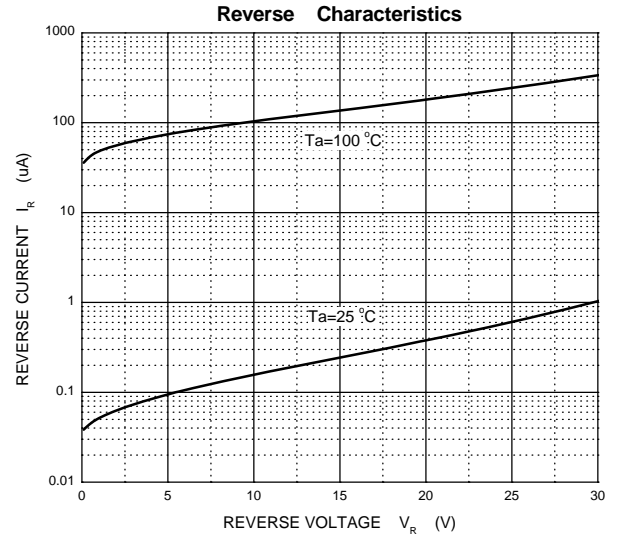
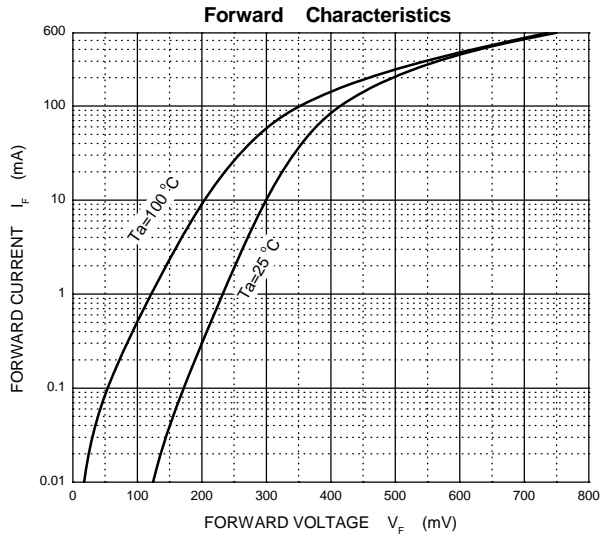
#### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	$V_F$	0.6	V
Reverse Current at $V_R = 10\text{ V}$	$I_R$	1	$\mu\text{A}$

Note: ESD sensitive product handling required.

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## Typical Characteristics

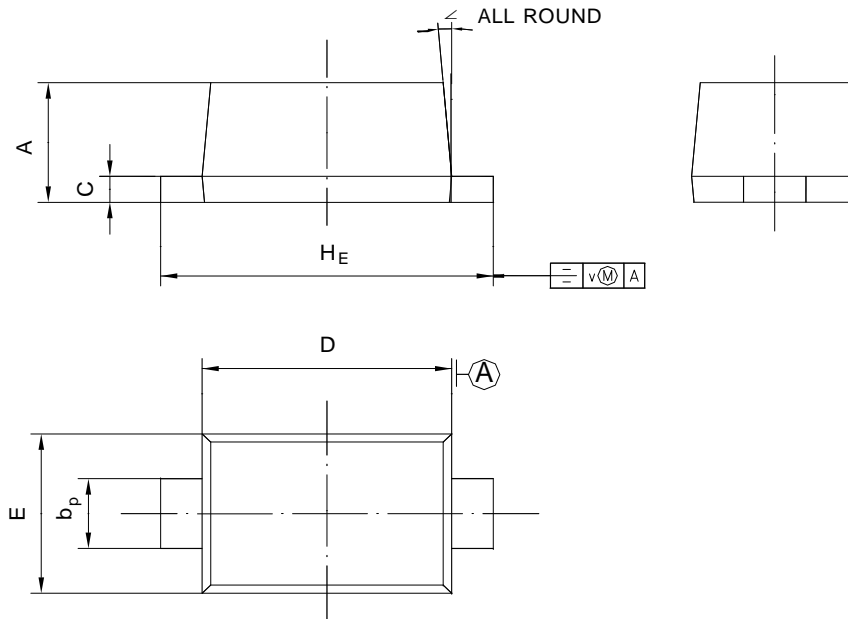


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## PACKAGE OUTLINE

SOD-523

Plastic surface mounted package; 2 leads



UNIT	A	$b_p$	C	D	E	$H_E$	V	$\angle$
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°